



# JCS20N65H

## 主要参数 MAIN CHARACTERISTICS

$I_D$	20A
$V_{DS}$	650 V
$R_{DS(on)}$ -max (@ $V_{GS}=10V$ )	0.5 $\Omega$
$Q_g$ -typ	45nC

### 用途

- 高频开关电源
- 电子镇流器
- LED 电源

### APPLICATIONS

- High frequency switching mode power supply
- Electronic ballast
- LED power supply

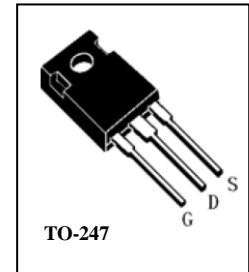
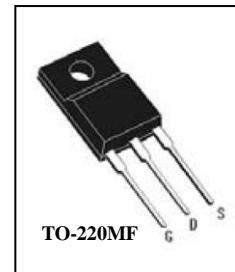
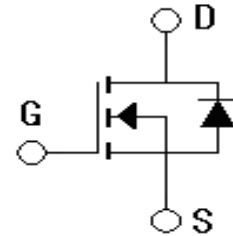
### 产品特性

- 低栅极电荷
- 低  $C_{RSS}$  (典型值 11pF)
- 开关速度快
- 产品全部经过雪崩测试
- 高抗  $dv/dt$  能力
- RoHS 产品

### FEATURES

- Low gate charge
- Low  $C_{RSS}$  (typical 11pF)
- Fast switching
- 100% avalanche tested
- Improved  $dv/dt$  capability
- RoHS product

## 封装 Package



## 订货信息 ORDER MESSAGE

订货型号 Order codes	印记 Marking	封装 Package	无卤素 Halogen Free	包装 Packaging	器件重量 Device Weight
JCS20N65WH-O-W-N-B	JCS20N65WH	TO-247	否 NO	条管 Tube	5.20 g(typ)
JCS20N65FH-O-F-N-B	JCS20N65FH	TO-220MF	否 NO	条管 Tube	2.20 g(typ)
JCS20N65FH-R-F-N-B	JCS20N65FH	TO-220MF	是 YES	条管 Tube	2.20 g(typ)





## 绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项 目 Parameter	符 号 Symbol	数 值 Value		单 位 Unit
		JCS20N65WH	JCS20N65FH	
最高漏极—源极直流电压 Drain-Source Voltage	$V_{DSS}$	650		V
连续漏极电流 Drain Current -continuous	$I_D$ T=25°C	20		A
	T=100°C	12.5		A
最大脉冲漏极电流 (注 1) Drain Current – pulse (note 1)	$I_{DM}$	80		A
最高栅源电压 Gate-Source Voltage	$V_{GSS}$	±30		V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	$E_{AS}$	108		mJ
雪崩电流 (注 1) Avalanche Current (note 1)	$I_{AR}$	20		A
重复雪崩能量 (注 1) Repetitive Avalanche Energy (note 1)	$E_{AR}$	20.7		mJ
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	50		V/ns
耗散功率 Power Dissipation	$P_D$ T <sub>C</sub> =25°C -Derate above 25°C	500	62.2	W
		4.0	0.5	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~+150		°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T <sub>L</sub>	300		°C

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature





项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
<b>关态特性 Off –Characteristics</b>						
漏—源击穿电压 Drain-Source Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	650	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$ , referenced to $25^\circ C$	-	0.5	-	$V/^\circ C$
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=650V, V_{GS}=0V,$ $T_C=25^\circ C$	-	-	10	$\mu A$
		$V_{DS}=520V, T_C=125^\circ C$	-	-	100	$\mu A$
正向栅极体漏电流 Gate-body leakage current, forward	$I_{GSSF}$	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	$I_{GSSR}$	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
<b>通态特性 On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	3.0	-	5.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D=10A$	-	0.44	0.5	$\Omega$
<b>动态特性 Dynamic Characteristics</b>						
输入电容 Input capacitance	$C_{iss}$	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$	-	2550	4000	pF
输出电容 Output capacitance	$C_{oss}$		-	250		pF
反向传输电容 Reverse transfer capacitance	$C_{rss}$		-	11		pF





## 电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	$t_d(\text{on})$	$V_{DD}=300V, I_D=20A, R_G=25\Omega$ (note 4, 5)	-	56	128	ns
上升时间 Turn-On rise time	$t_r$		-	140	270	ns
延迟时间 Turn-Off delay time	$t_d(\text{off})$		-	80	350	ns
下降时间 Turn-Off Fall time	$t_f$		-	50	120	ns
栅极电荷总量 Total Gate Charge	$Q_g$	$V_{DS}=520V,$ $I_D=20A$ $V_{GS}=10V$ (note 4, 5)	-	45	80	nC
栅-源电荷 Gate-Source charge	$Q_{gs}$		-	15.0	-	nC
栅-漏电荷 Gate-Drain charge	$Q_{gd}$		-	17	-	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain-Source Diode Forward Current		$I_S$	-	-	20	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		$I_{SM}$	-	-	80	A
正向压降 Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V,$ $I_S=20A$	-	-	1.45	V
反向恢复时间 Reverse recovery time	$t_{rr}$	$V_{GS}=0V, I_S=20A$ $di_f/dt=100A/\mu s$ (note 4)	-	660	-	ns
反向恢复电荷 Reverse recovery charge	$Q_{rr}$		-	.9.3	-	$\mu C$

## 热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max		单 位 Unit
		JCS20N65WH	JCS20N65FH	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.25	2.01	$^{\circ}C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	29.8	39.7	$^{\circ}C/W$

注释:

- 1: 脉冲宽度由最高结温限制
- 2:  $L=0.5mH, I_{AS}=20A, V_{DD}=50V, R_G=25\Omega$ , 起始结温  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 9.5A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$ , 起始结温  $T_J=25^{\circ}C$
- 4: 脉冲测试: 脉冲宽度  $\leq 300\mu s$ , 占空比  $\leq 2\%$
- 5: 基本与工作温度无关

Notes:

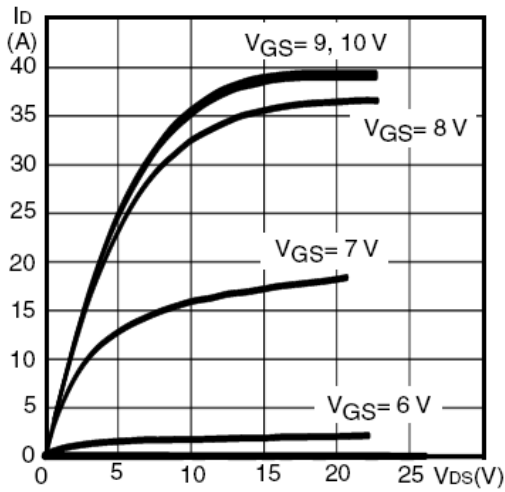
- 1: Pulse width limited by maximum junction temperature
- 2:  $L=0.5mH, I_{AS}=20A, V_{DD}=50V, R_G=25\Omega$ , Starting  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 9.5A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$
- 5: Essentially independent of operating temperature



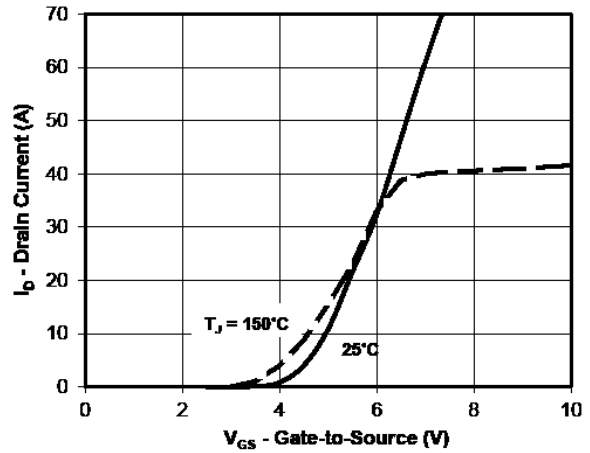


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

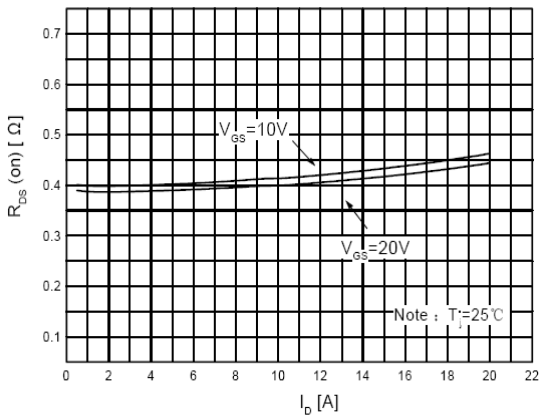
On-Region Characteristics



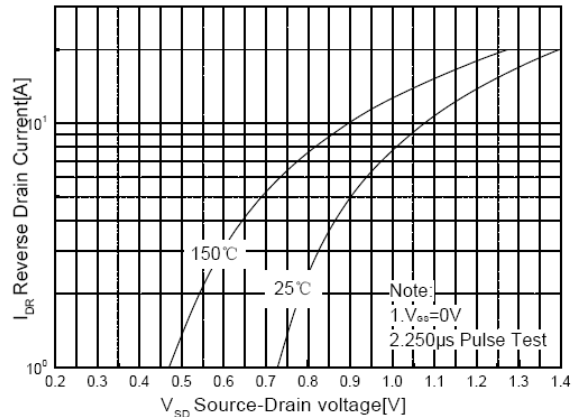
Transfer Characteristics



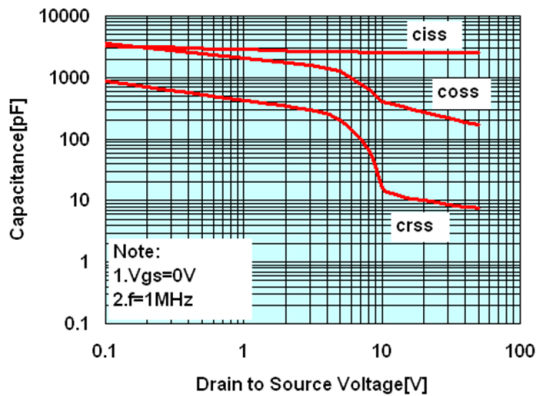
On-Resistance Variation vs. Drain Current and Gate Voltage



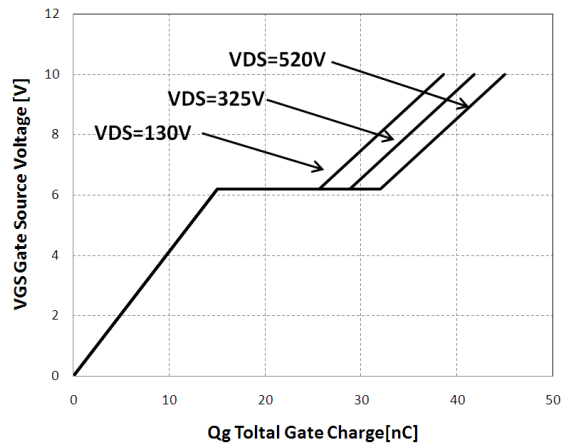
Body Diode Forward Voltage Variation vs. Source Current and Temperature



Capacitance Characteristics



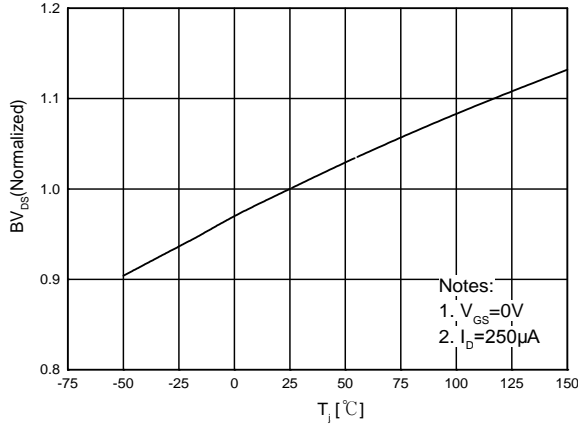
Gate Charge Characteristics



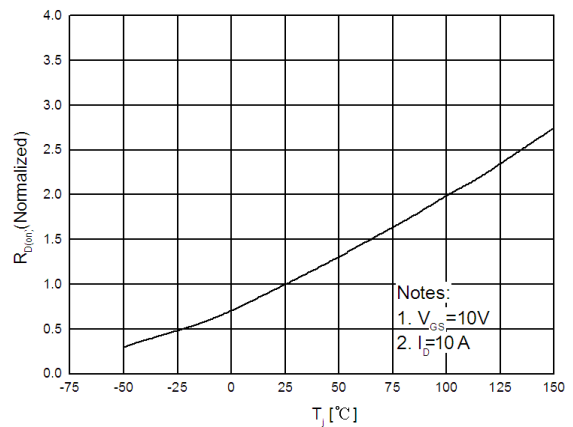


### 特征曲线 ELECTRICAL CHARACTERISTICS (curves)

#### Breakdown Voltage Variation vs. Temperature



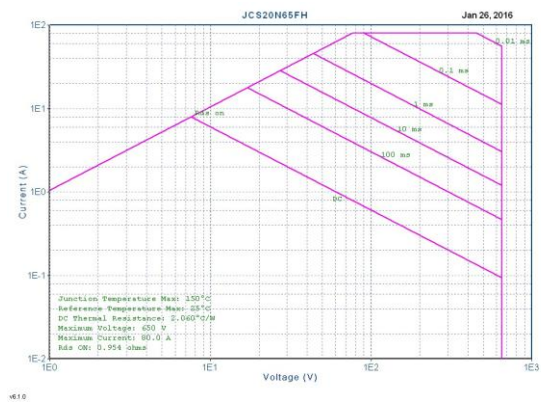
#### On-Resistance Variation vs. Temperature



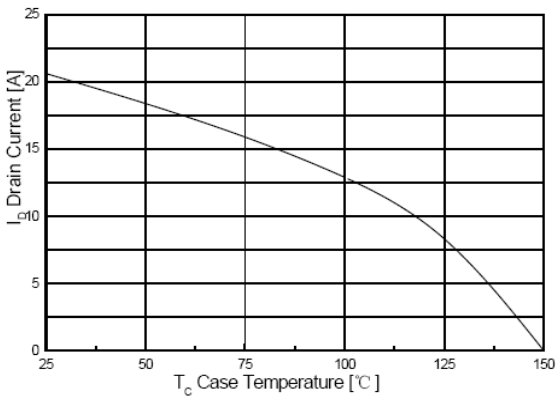
#### Maximum Safe Operating Area For JCS20N65WH



#### Maximum Safe Operating Area For JCS20N65FH

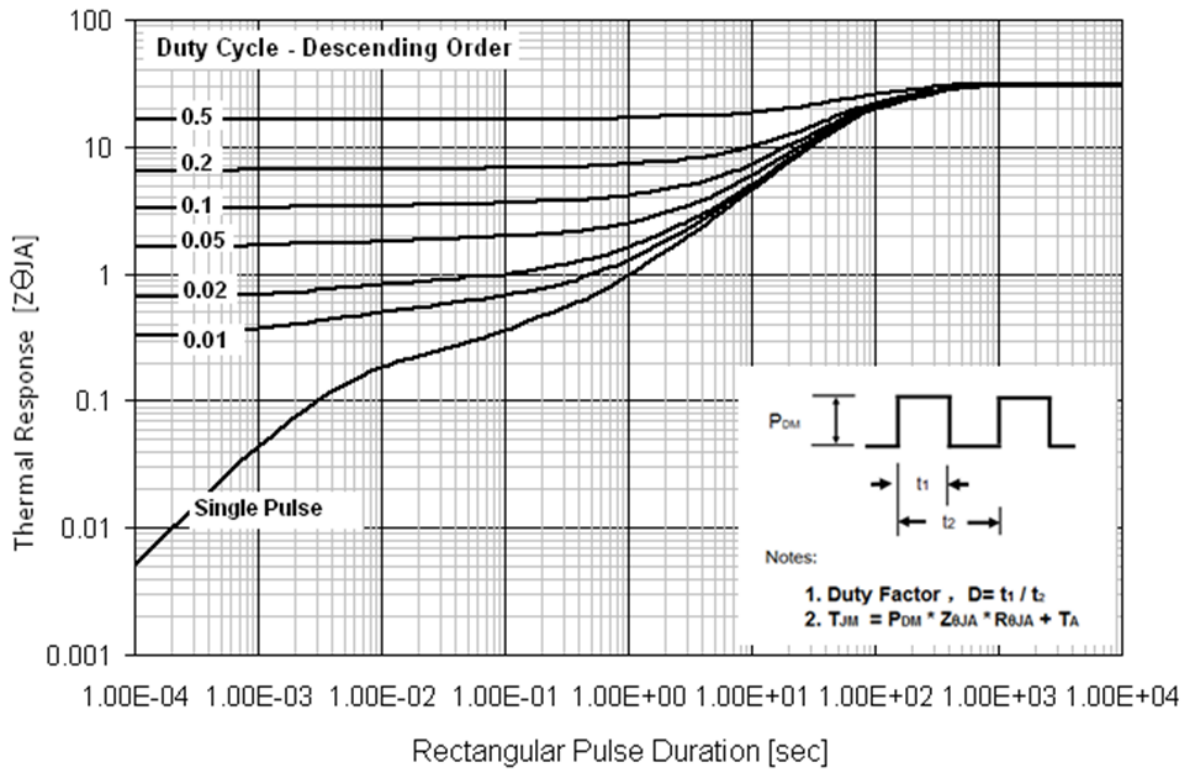
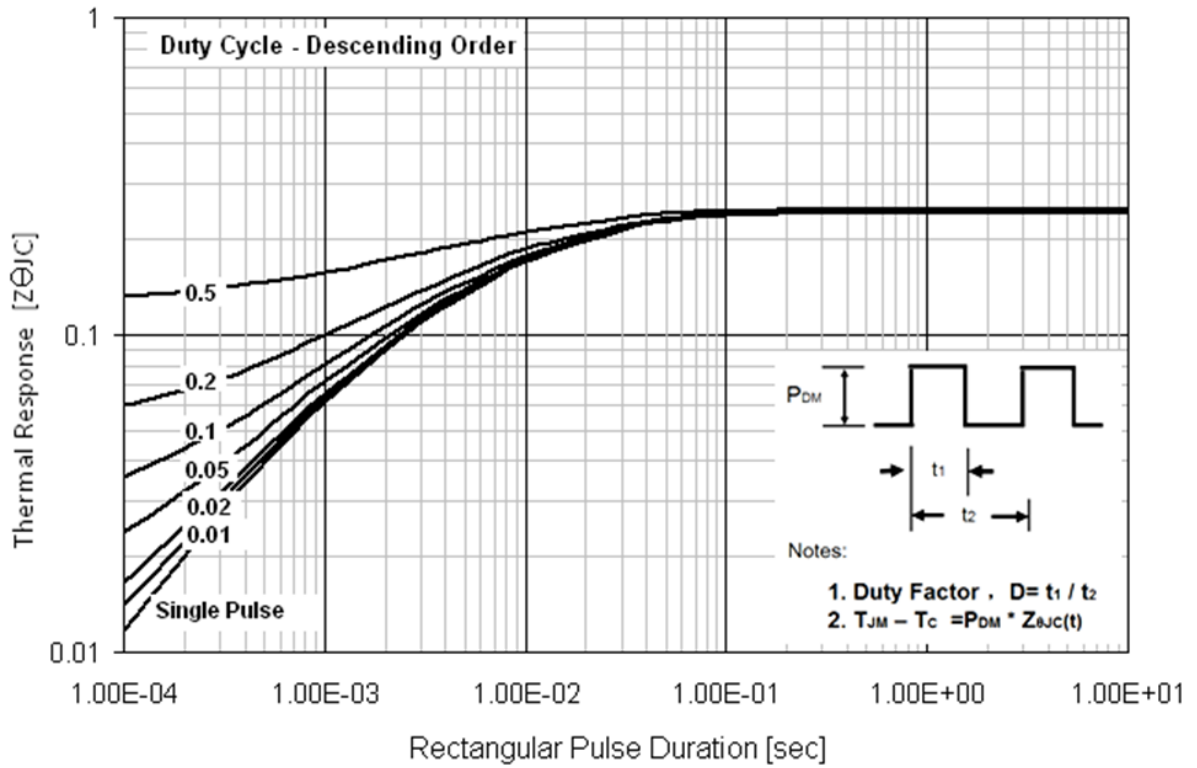


#### Maximum Drain Current vs. Case Temperature



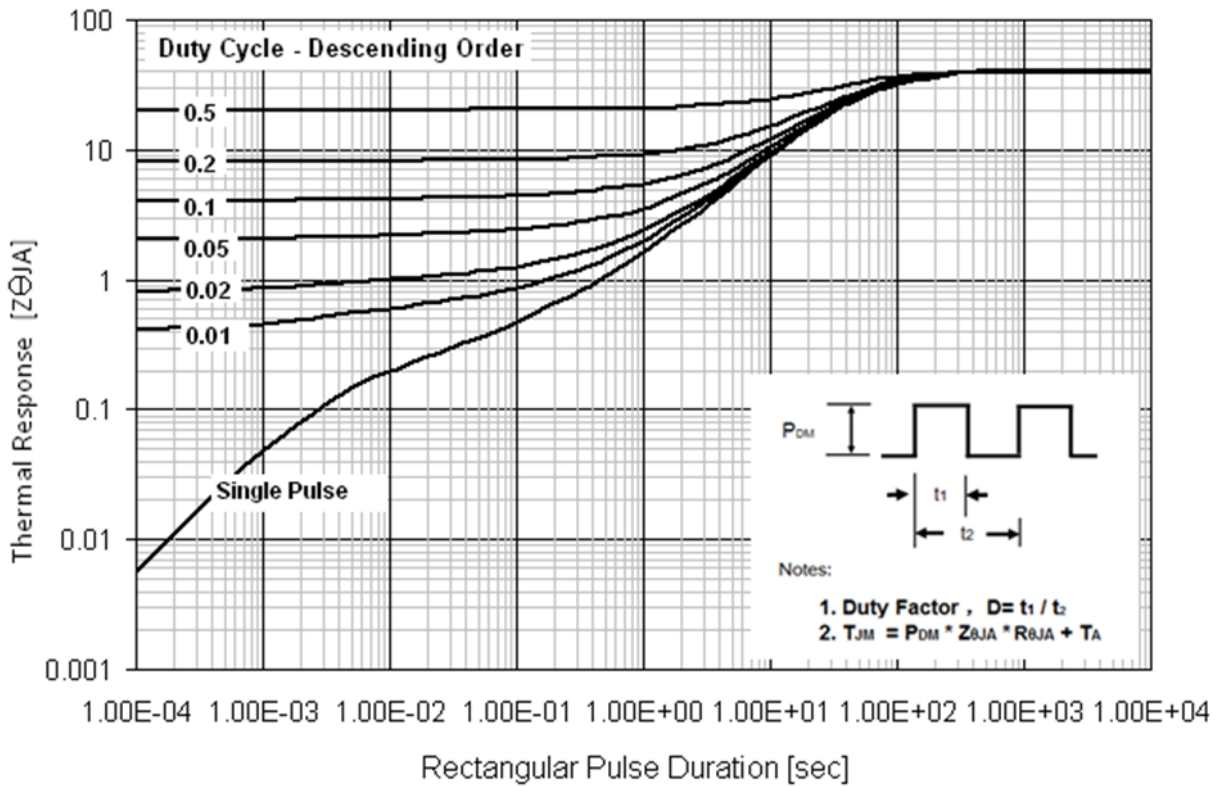
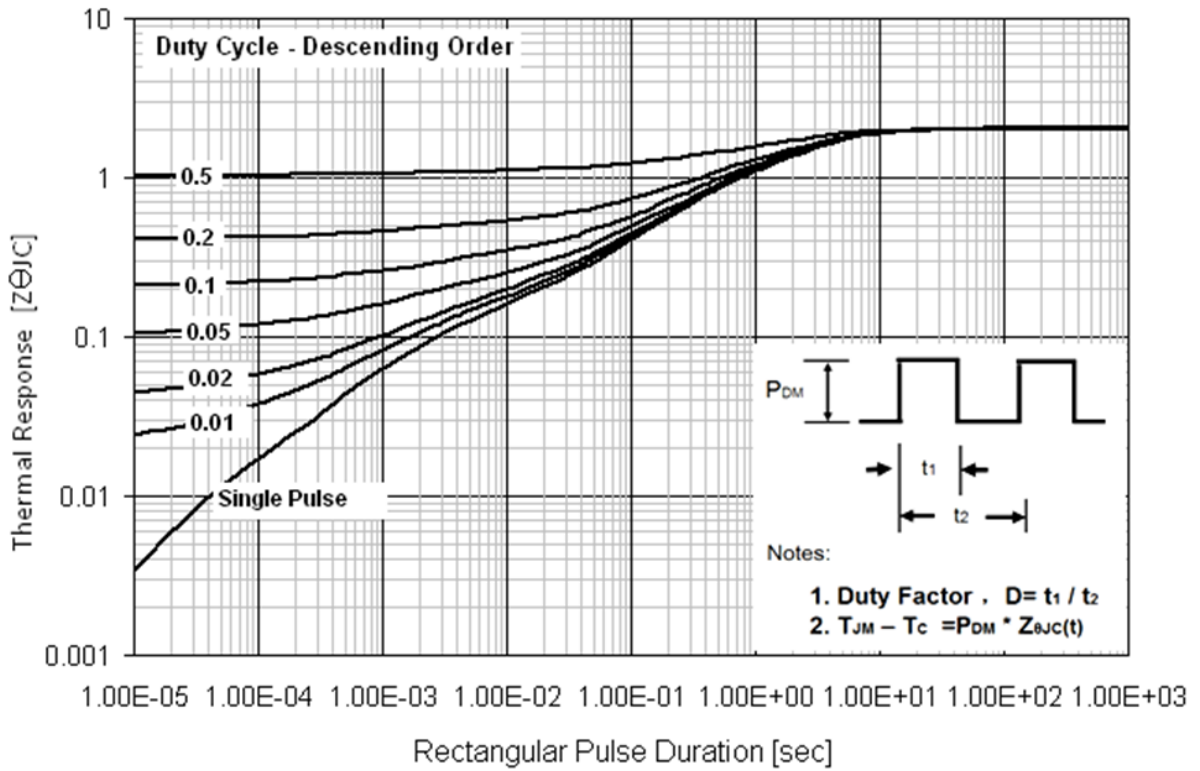


Transient Thermal Response Curve  
For JCS20N65WH





Transient Thermal Response Curve For JCS20N65FH

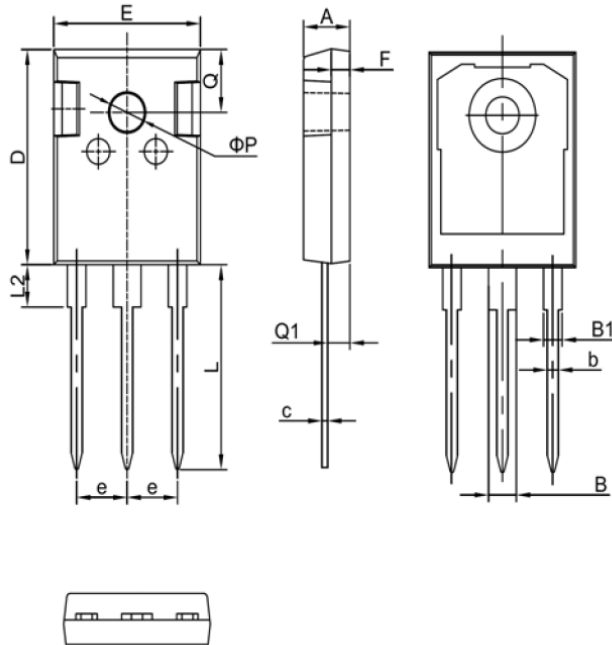






TO-247

单位 Unit: mm



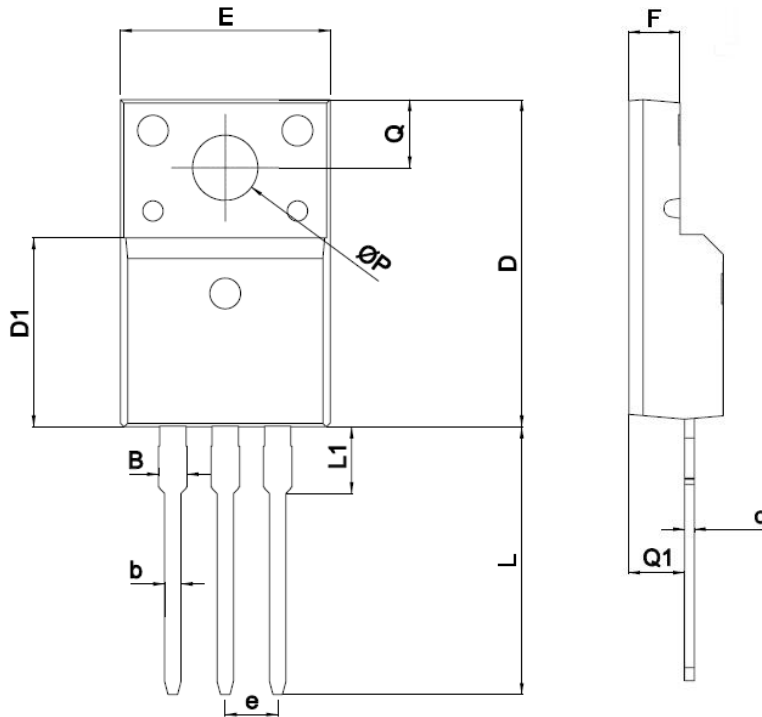
符号 symbol	MIN	MAX
A	4.90	5.10
B	2.95	3.35
B1	1.95	2.35
b	1.15	1.35
c	0.50	0.70
D	20.90	21.10
E	15.70	15.90
e	5.34	5.54
F	1.90	2.10
L	19.40	20.40
L2	4.03	4.23
Q	6.00	6.40
Q1	2.30	2.50
P	3.50	3.70



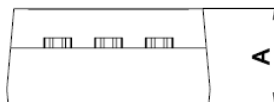


## TO-220MF

单位 Unit: mm



SYMBOL	mm	
	MIN	MAX
A	4.5	4.9
B		1.47
b	0.7	0.9
c	0.45	0.60
D	15.67	16.07
D1	9.04	9.20
e	2.54TYPE	
E	9.96	10.36
F	2.34	2.74
L	12.58	13.38
L1	3.13	3.33
Q	3.2	3.4
Q1	2.56	2.96
ΦP	3.08	3.28



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